

IS61NLF12836A/IS61NVF12836A IS61NLF25618A/IS61NVF25618A



128K x 36 and 256K x 18 4Mb, FLOW THROUGH 'NO WAIT' STATE BUS SRAM

AUGUST 2011

FEATURES

- 100 percent bus utilization
- No wait cycles between Read and Write
- Internal self-timed write cycle
- Individual Byte Write Control
- Single Read/Write control pin
- Clock controlled, registered address, data and control
- Interleaved or linear burst sequence control using MODE input
- Three chip enables for simple depth expansion and address pipelining
- Power Down mode
- Common data inputs and data outputs
- $\overline{\text{CKE}}$ pin to enable clock and suspend operation
- JEDEC 100-pin TQFP, 119-ball PBGA, and 165-ball PBGA packages
- Power supply:
NVF: $V_{\text{DD}} 2.5\text{V} (\pm 5\%)$, $V_{\text{DDQ}} 2.5\text{V} (\pm 5\%)$
NLF: $V_{\text{DD}} 3.3\text{V} (\pm 5\%)$, $V_{\text{DDQ}} 3.3\text{V}/2.5\text{V} (\pm 5\%)$
- Industrial temperature available
- Lead-free available

DESCRIPTION

The 4 Meg 'NLF/NVF' product family feature high-speed, low-power synchronous static RAMs designed to provide a burstable, high-performance, 'no wait' state, device for networking and communications applications. They are organized as 128K words by 36 bits and 256K words by 18 bits, fabricated with ISSI's advanced CMOS technology.

Incorporating a 'no wait' state feature, wait cycles are eliminated when the bus switches from read to write, or write to read. This device integrates a 2-bit burst counter, high-speed SRAM core, and high-drive capability outputs into a single monolithic circuit.

All synchronous inputs pass through registers are controlled by a positive-edge-triggered single clock input. Operations may be suspended and all synchronous inputs ignored when Clock Enable, $\overline{\text{CKE}}$ is HIGH. In this state the internal device will hold their previous values.

All Read, Write and Deselect cycles are initiated by the ADV input. When the ADV is HIGH the internal burst counter is incremented. New external addresses can be loaded when ADV is LOW.

Write cycles are internally self-timed and are initiated by the rising edge of the clock inputs and when $\overline{\text{WE}}$ is LOW. Separate byte enables allow individual bytes to be written.

A burst mode pin (MODE) defines the order of the burst sequence. When tied HIGH, the interleaved burst sequence is selected. When tied LOW, the linear burst sequence is selected.

FAST ACCESS TIME

| Symbol | Parameter | 6.5 | 7.5 | Units |
|-----------------|-------------------|-----|-----|-------|
| t_{KQ} | Clock Access Time | 6.5 | 7.5 | ns |
| t_{KC} | Cycle Time | 7.5 | 8.5 | ns |
| | Frequency | 133 | 117 | MHz |

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- a.) the risk of injury or damage has been minimized;
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BLOCK DIAGRAM





Bottom View
119-Ball, 14 mm x 22 mm BGA



Bottom View
165-Ball, 13 mm x 15mm BGA

PIN CONFIGURATION — 128K x 36, 165-Ball PBGA (TOP VIEW)

| | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 11 |
|---|------|-----|-----------------|------------------|------------------|------------------|------------------|-----------------|------|-----|------|
| A | NC | A | \overline{CE} | \overline{BWc} | \overline{BWb} | $\overline{CE2}$ | \overline{CKE} | ADV | NC | A | NC |
| B | NC | A | CE2 | \overline{BWd} | \overline{BWa} | CLK | \overline{WE} | \overline{OE} | NC | A | NC |
| C | DQPc | NC | VDDQ | VSS | VSS | VSS | VSS | VSS | VDDQ | NC | DQPb |
| D | DQc | DQc | VDDQ | VDD | VSS | VSS | VSS | VDD | VDDQ | DQb | DQb |
| E | DQc | DQc | VDDQ | VDD | VSS | VSS | VSS | VDD | VDDQ | DQb | DQb |
| F | DQc | DQc | VDDQ | VDD | VSS | VSS | VSS | VDD | VDDQ | DQb | DQb |
| G | DQc | DQc | VDDQ | VDD | VSS | VSS | VSS | VDD | VDDQ | DQb | DQb |
| H | NC | NC | NC | VDD | VSS | VSS | VSS | VDD | NC | NC | ZZ |
| J | DQd | DQd | VDDQ | VDD | VSS | VSS | VSS | VDD | VDDQ | DQa | DQa |
| K | DQd | DQd | VDDQ | VDD | VSS | VSS | VSS | VDD | VDDQ | DQa | DQa |
| L | DQd | DQd | VDDQ | VDD | VSS | VSS | VSS | VDD | VDDQ | DQa | DQa |
| M | DQd | DQd | VDDQ | VDD | VSS | VSS | VSS | VDD | VDDQ | DQa | DQa |
| N | DQPd | NC | VDDQ | VSS | NC | NC | NC | VSS | VDDQ | NC | DQPa |
| P | NC | NC | A | A | NC | A1* | NC | A | A | A | NC |
| R | MODE | NC | A | A | NC | A0* | NC | A | A | A | A |

Note: A0 and A1 are the two least significant bits (LSB) of the address field and set the internal burst counter if burst is desired.

PIN DESCRIPTIONS

| Symbol | Pin Name |
|--|--|
| A | Address Inputs |
| A0, A1 | Synchronous Burst Address Inputs |
| ADV | Synchronous Burst Address Advance/Load |
| \overline{WE} | Synchronous Read/Write Control Input |
| CLK | Synchronous Clock |
| \overline{CKE} | Clock Enable |
| \overline{CE} , $\overline{CE2}$, CE2 | Synchronous Chip Enable |
| \overline{BWx} (x=a-d) | Synchronous Byte Write Inputs |
| \overline{OE} | Output Enable |
| ZZ | Power Sleep Mode |

| | |
|------|---|
| MODE | Burst Sequence Selection |
| VDD | 3.3V/2.5V Power Supply |
| NC | No Connect |
| DQx | Data Inputs/Outputs |
| DQPx | Parity Data I/O |
| VDDQ | Isolated output Power Supply 3.3V/2.5V |
| VSS | Ground |

119-PIN PBGA PACKAGE CONFIGURATION —128K x 36 (TOP VIEW)

| | 1 | 2 | 3 | 4 | 5 | 6 | 7 |
|---|------------------|------------------|--------------------------|-------------------------|--------------------------|-------------------------|------------------|
| A | V _{DDQ} | A | A | NC | A | A | V _{DDQ} |
| B | NC | CE2 | A | ADV | A | $\overline{\text{CE2}}$ | NC |
| C | NC | A | A | V _{DD} | A | A | NC |
| D | DQ _c | DQP _c | V _{SS} | NC | V _{SS} | DQP _b | DQ _b |
| E | DQ _c | DQ _c | V _{SS} | $\overline{\text{CE}}$ | V _{SS} | DQ _b | DQ _b |
| F | V _{DDQ} | DQ _c | V _{SS} | $\overline{\text{OE}}$ | V _{SS} | DQ _b | V _{DDQ} |
| G | DQ _c | DQ _c | $\overline{\text{BW}}_c$ | NC | $\overline{\text{BW}}_b$ | DQ _b | DQ _b |
| H | DQ _c | DQ _c | V _{SS} | $\overline{\text{WE}}$ | V _{SS} | DQ _b | DQ _b |
| J | V _{DDQ} | V _{DD} | NC | V _{DD} | NC | V _{DD} | V _{DDQ} |
| K | DQ _d | DQ _d | V _{SS} | CLK | V _{SS} | DQ _a | DQ _a |
| L | DQ _d | DQ _d | $\overline{\text{BW}}_d$ | NC | $\overline{\text{BW}}_a$ | DQ _a | DQ _a |
| M | V _{DDQ} | DQ _d | V _{SS} | $\overline{\text{CKE}}$ | V _{SS} | DQ _a | V _{DDQ} |
| N | DQ _d | DQ _d | V _{SS} | A ₁ * | V _{SS} | DQ _a | DQ _a |
| P | DQ _d | DQP _d | V _{SS} | A ₀ * | V _{SS} | DQP _a | DQ _a |
| R | NC | A | MODE | V _{DD} | NC | A | NC |
| T | NC | NC | A | A | A | NC | ZZ |
| U | V _{DDQ} | NC | NC | NC | NC | NC | V _{DDQ} |

Note: A0 and A1 are the two least significant bits (LSB) of the address field and set the internal burst counter if burst is desired.

PIN DESCRIPTIONS

| Symbol | Pin Name |
|----------------------------------|--|
| A | Address Inputs |
| A0, A1 | Synchronous Burst Address Inputs |
| ADV | Synchronous Burst Address Advance/Load |
| $\overline{\text{WE}}$ | Synchronous Read/Write Control Input |
| CLK | Synchronous Clock |
| $\overline{\text{CKE}}$ | Clock Enable |
| $\overline{\text{CE}}$ | Synchronous Chip Select |
| $\overline{\text{CE2}}$ | Synchronous Chip Select |
| CE2 | Synchronous Chip Select |
| $\overline{\text{BW}}_x$ (x=a-d) | Synchronous Byte Write Inputs |

| | |
|----------------------------------|--------------------------|
| $\overline{\text{OE}}$ | Output Enable |
| ZZ | Power Sleep Mode |
| MODE | Burst Sequence Selection |
| V _{DD} | Power Supply |
| V _{SS} | Ground |
| NC | No Connect |
| DQ _a -DQ _d | Data Inputs/Outputs |
| DQP _a -Pd | Parity Data I/O |
| V _{DDQ} | Output Power Supply |

165-PIN PBGA PACKAGE CONFIGURATION —256K x 18 (TOP VIEW)

| | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 10 | 11 |
|---|------------------|-----------------|-----------------|------------------|------------------|------------------|------------------|-----------------|------|-----------------|------------------|
| A | NC | A | \overline{CE} | \overline{BWb} | NC | $\overline{CE2}$ | \overline{CKE} | ADV | NC | A | A |
| B | NC | A | CE2 | NC | \overline{BWa} | CLK | \overline{WE} | \overline{OE} | NC | A | NC |
| C | NC | NC | VDDQ | Vss | Vss | Vss | Vss | Vss | VDDQ | NC | DQP _a |
| D | NC | DQ _b | VDDQ | VDD | Vss | Vss | Vss | VDD | VDDQ | NC | DQ _a |
| E | NC | DQ _b | VDDQ | VDD | Vss | Vss | Vss | VDD | VDDQ | NC | DQ _a |
| F | NC | DQ _b | VDDQ | VDD | Vss | Vss | Vss | VDD | VDDQ | NC | DQ _a |
| G | NC | DQ _b | VDDQ | VDD | Vss | Vss | Vss | VDD | VDDQ | NC | DQ _a |
| H | NC | NC | NC | VDD | Vss | Vss | Vss | VDD | NC | NC | ZZ |
| J | DQ _b | NC | VDDQ | VDD | Vss | Vss | Vss | VDD | VDDQ | DQ _a | NC |
| K | DQ _b | NC | VDDQ | VDD | Vss | Vss | Vss | VDD | VDDQ | DQ _a | NC |
| L | DQ _b | NC | VDDQ | VDD | Vss | Vss | Vss | VDD | VDDQ | DQ _a | NC |
| M | DQ _b | NC | VDDQ | VDD | Vss | Vss | Vss | VDD | VDDQ | DQ _a | NC |
| N | DQP _b | NC | VDDQ | Vss | NC | NC | NC | Vss | VDDQ | NC | NC |
| P | NC | NC | A | A | NC | A ₁ * | NC | A | A | A | NC |
| R | MODE | NC | A | A | NC | A ₀ * | NC | A | A | A | A |

Note: A0 and A1 are the two least significant bits (LSB) of the address field and set the internal burst counter if burst is desired.

PIN DESCRIPTIONS

| Symbol | Pin Name |
|--|--|
| A | Address Inputs |
| A0, A1 | Synchronous Burst Address Inputs |
| ADV | Synchronous Burst Address Advance/Load |
| \overline{WE} | Synchronous Read/Write Control Input |
| CLK | Synchronous Clock |
| \overline{CKE} | Clock Enable |
| \overline{CE} , $\overline{CE2}$, CE2 | Synchronous Chip Enable |
| \overline{BWx} (x=a,b) | Synchronous Byte Write Inputs |
| \overline{OE} | Output Enable |
| ZZ | Power Sleep Mode |

| | |
|------------------|---|
| MODE | Burst Sequence Selection |
| VDD | 3.3V/2.5V Power Supply |
| NC | No Connect |
| DQ _x | Data Inputs/Outputs |
| DQP _x | Parity Data I/O |
| VDDQ | Isolated output Power Supply 3.3V/2.5V |
| Vss | Ground |

119-PIN PBGA PACKAGE CONFIGURATION —256K x 18 (TOP VIEW)

| | 1 | 2 | 3 | 4 | 5 | 6 | 7 |
|---|------|------|------------------|------------------|------------------|------------------|------|
| A | VDDQ | A | A | NC | A | A | VDDQ |
| B | NC | CE2 | A | ADV | A | $\overline{CE2}$ | NC |
| C | NC | A | A | VDD | A | A | NC |
| D | DQb | NC | VSS | NC | VSS | DQPa | NC |
| E | NC | DQb | VSS | \overline{CE} | VSS | NC | DQa |
| F | VDDQ | NC | VSS | \overline{OE} | VSS | DQa | VDDQ |
| G | NC | DQb | \overline{BWb} | NC | NC | NC | DQa |
| H | DQb | NC | VSS | \overline{WE} | VSS | DQa | NC |
| J | VDDQ | VDD | NC | VDD | NC | VDD | VDDQ |
| K | NC | DQb | VSS | CLK | VSS | NC | DQa |
| L | DQb | NC | NC | NC | \overline{BWa} | DQa | NC |
| M | VDDQ | DQb | VSS | \overline{CKE} | VSS | NC | VDDQ |
| N | DQb | NC | VSS | A1* | VSS | DQa | NC |
| P | NC | DQPb | VSS | A0* | VSS | NC | DQa |
| R | NC | A | MODE | VDD | NC | A | NC |
| T | NC | A | A | NC | A | A | ZZ |
| U | VDDQ | NC | NC | NC | NC | NC | VDDQ |

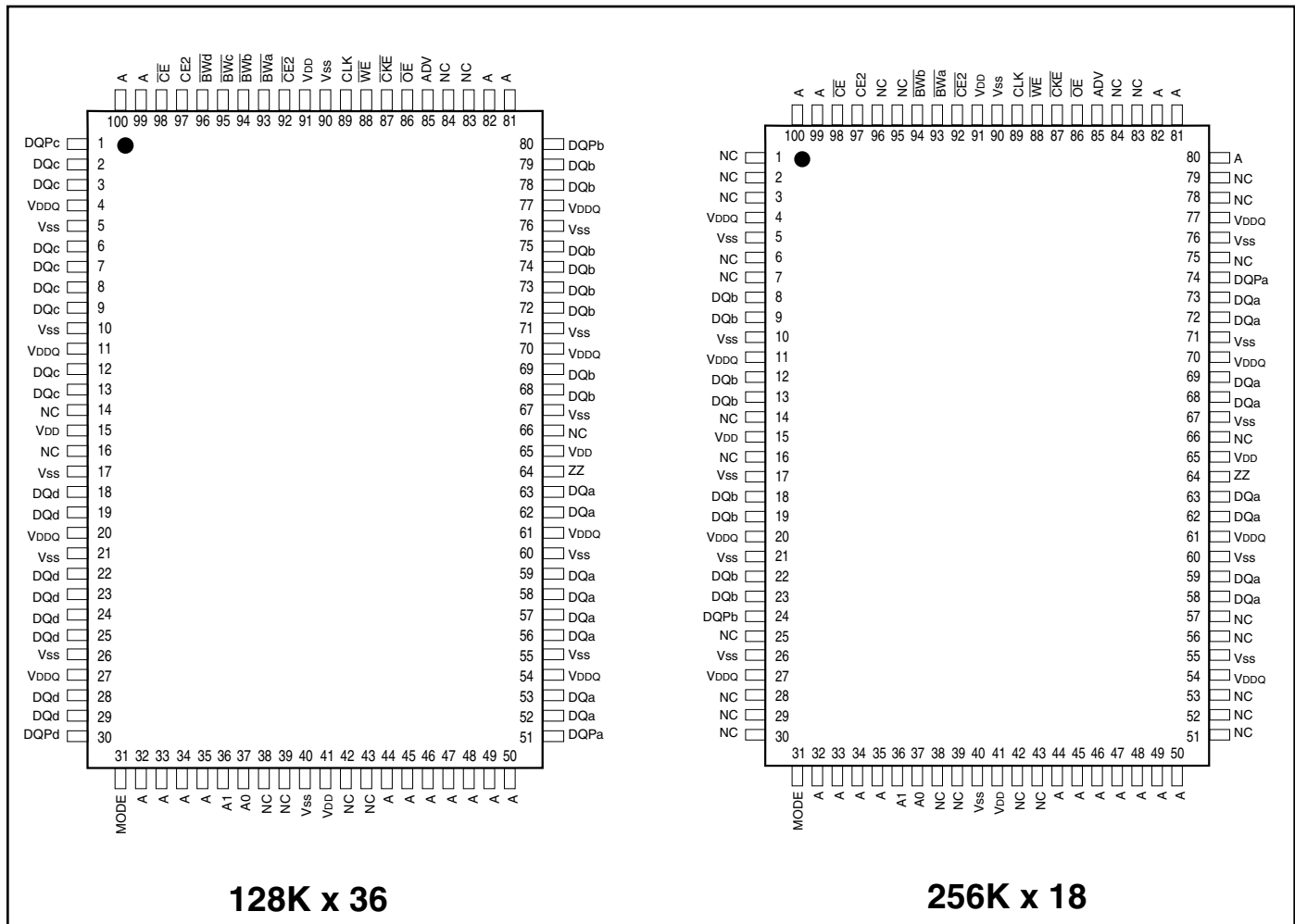
Note: A0 and A1 are the two least significant bits (LSB) of the address field and set the internal burst counter if burst is desired.

PIN DESCRIPTIONS

| Symbol | Pin Name |
|--------------------------|--|
| A | Address Inputs |
| A0, A1 | Synchronous Burst Address Inputs |
| ADV | Synchronous Burst Address Advance/Load |
| \overline{WE} | Synchronous Read/Write Control Input |
| CLK | Synchronous Clock |
| \overline{CKE} | Clock Enable |
| \overline{CE} | Synchronous Chip Select |
| $\overline{CE2}$ | Synchronous Chip Select |
| CE2 | Synchronous Chip Select |
| \overline{BWx} (x=a,b) | Synchronous Byte Write Inputs |

| | |
|-----------------|--------------------------|
| \overline{OE} | Output Enable |
| ZZ | Power Sleep Mode |
| MODE | Burst Sequence Selection |
| VDD | Power Supply |
| VSS | Ground |
| NC | No Connect |
| DQa-DQb | Data Inputs/Outputs |
| DQPa-Pb | Parity Data I/O |
| VDDQ | Output Power Supply |

PIN CONFIGURATION
100-Pin TQFP

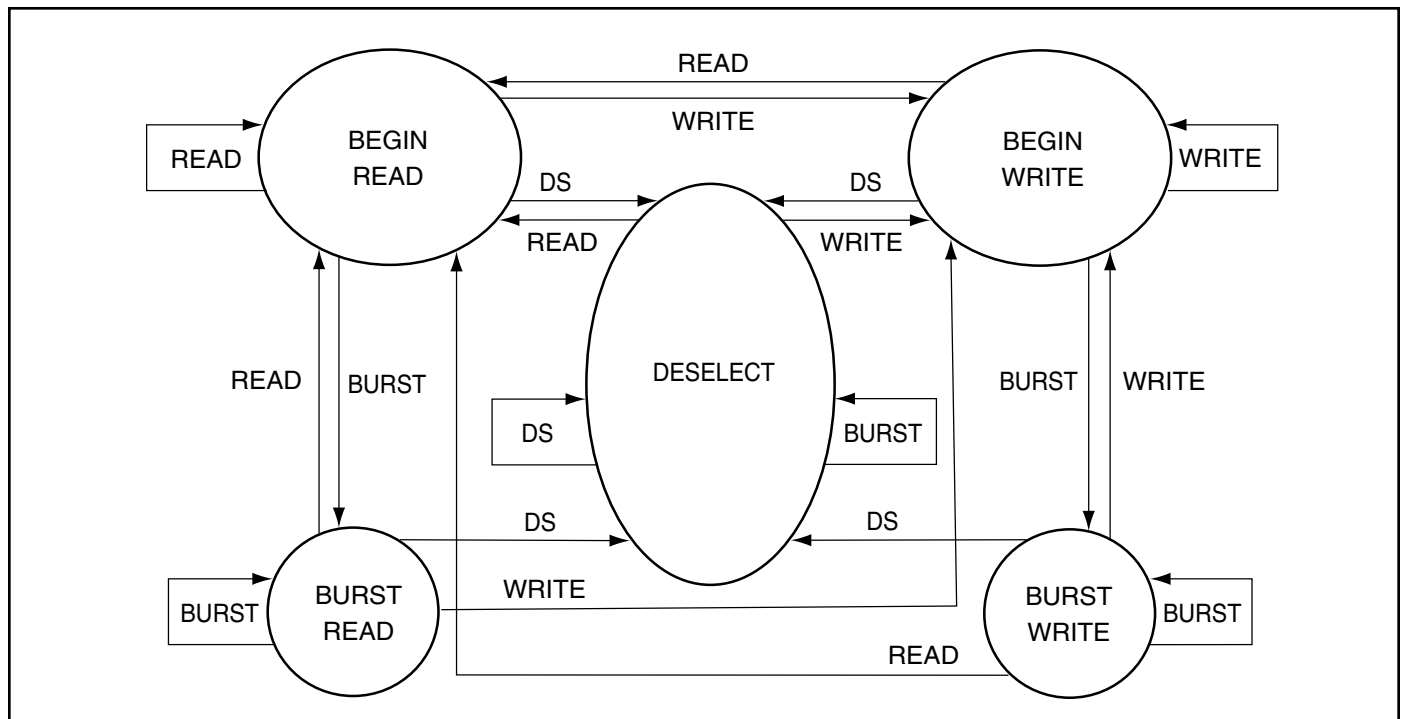


PIN DESCRIPTIONS

| | |
|----------------------------------|---|
| A0, A1 | Synchronous Address Inputs. These pins must be tied to the two LSBs of the address bus. |
| A | Synchronous Address Inputs |
| CLK | Synchronous Clock |
| ADV | Synchronous Burst Address Advance |
| BW _a -BW _d | Synchronous Byte Write Enable |
| WE | Write Enable |
| CKE | Clock Enable |
| Vss | Ground for Core |
| NC | Not Connected |

| | |
|------------------------------------|---|
| CE, CE2, CE ₂ | Synchronous Chip Enable |
| OE | Output Enable |
| DQ _a -DQ _d | Synchronous Data Input/Output |
| DQP _a -DQP _d | Parity Data I/O |
| MODE | Burst Sequence Selection |
| VDD | +3.3V/2.5V Power Supply |
| Vss | Ground for output Buffer |
| VDDQ | Isolated Output Buffer Supply: +3.3V/2.5V |
| ZZ | Snooze Enable |

STATE DIAGRAM



SYNCHRONOUS TRUTH TABLE⁽¹⁾

| Operation | Address Used | \overline{CE} | CE2 | $\overline{CE2}$ | ADV | \overline{WE} | \overline{BWx} | \overline{OE} | \overline{CKE} | CLK |
|-----------------------|------------------|-----------------|-----|------------------|-----|-----------------|------------------|-----------------|------------------|-----|
| Not Selected | N/A | H | X | X | L | X | X | X | L | ↑ |
| Not Selected | N/A | X | L | X | L | X | X | X | L | ↑ |
| Not Selected | N/A | X | X | H | L | X | X | X | L | ↑ |
| Not Selected Continue | N/A | X | X | X | H | X | X | X | L | ↑ |
| Begin Burst Read | External Address | L | H | L | L | H | X | L | L | ↑ |
| Continue Burst Read | Next Address | X | X | X | H | X | X | L | L | ↑ |
| NOP/Dummy Read | External Address | L | H | L | L | H | X | H | L | ↑ |
| Dummy Read | Next Address | X | X | X | H | X | X | H | L | ↑ |
| Begin Burst Write | External Address | L | H | L | L | L | L | X | L | ↑ |
| Continue Burst Write | Next Address | X | X | X | H | X | L | X | L | ↑ |
| NOP/Write Abort | N/A | L | H | L | L | L | H | X | L | ↑ |
| Write Abort | Next Address | X | X | X | H | X | H | X | L | ↑ |
| Ignore Clock | Current Address | X | X | X | X | X | X | X | H | ↑ |

Notes:

- "X" means don't care.
- The rising edge of clock is symbolized by ↑
- A continue deselect cycle can only be entered if a deselect cycle is executed first.
- $\overline{WE} = L$ means Write operation in Write Truth Table.
 $\overline{WE} = H$ means Read operation in Write Truth Table.
- Operation finally depends on status of asynchronous pins (\overline{ZZ} and \overline{OE}).

ASYNCHRONOUS TRUTH TABLE⁽¹⁾

| Operation | ZZ | \overline{OE} | I/O STATUS |
|------------|----|-----------------|-------------|
| Sleep Mode | H | X | High-Z |
| Read | L | L | DQ |
| | L | H | High-Z |
| Write | L | X | Din, High-Z |
| Deselected | L | X | High-Z |

Notes:

1. X means "Don't Care".
2. For write cycles following read cycles, the output buffers must be disabled with \overline{OE} , otherwise data bus contention will occur.
3. Sleep Mode means power Sleep Mode where stand-by current does not depend on cycle time.
4. Deselected means power Sleep Mode where stand-by current depends on cycle time.

WRITE TRUTH TABLE (x18)

| Operation | \overline{WE} | $\overline{Bw}a$ | $\overline{Bw}b$ |
|-----------------|-----------------|------------------|------------------|
| READ | H | X | X |
| WRITE BYTE a | L | L | H |
| WRITE BYTE b | L | H | L |
| WRITE ALL BYTES | L | L | L |
| WRITE ABORT/NOP | L | H | H |

Notes:

1. X means "Don't Care".
2. All inputs in this table must meet setup and hold time around the rising edge of CLK.

WRITE TRUTH TABLE (x36)

| Operation | \overline{WE} | \overline{BWa} | \overline{BWb} | \overline{BWc} | \overline{BWd} |
|-----------------|-----------------|------------------|------------------|------------------|------------------|
| READ | H | X | X | X | X |
| WRITE BYTE a | L | L | H | H | H |
| WRITE BYTE b | L | H | L | H | H |
| WRITE BYTE c | L | H | H | L | H |
| WRITE BYTE d | L | H | H | H | L |
| WRITE ALL BYTES | L | L | L | L | L |
| WRITE ABORT/NOF | L | H | H | H | H |

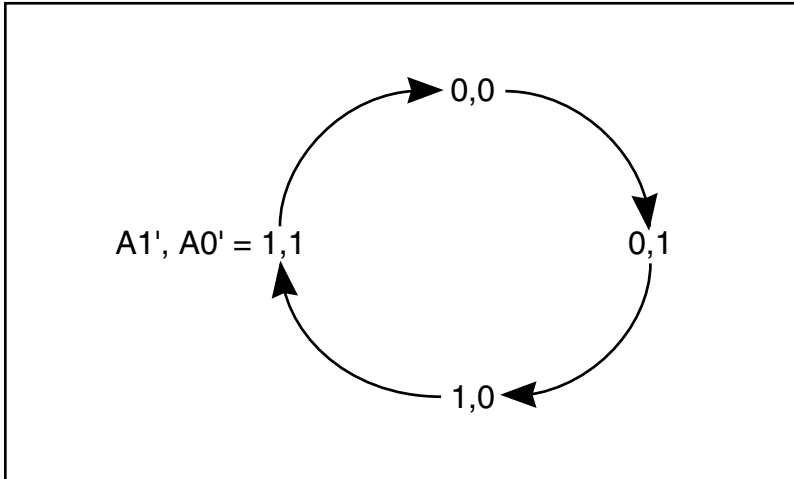
Notes:

1. X means "Don't Care".
2. All inputs in this table must be setup and hold time around the rising edge of CLK.

INTERLEAVED BURST ADDRESS TABLE (MODE = V_{DD} or NC)

| External Address A1 A0 | 1st Burst Address A1 A0 | 2nd Burst Address A1 A0 | 3rd Burst Address A1 A0 |
|---------------------------|----------------------------|----------------------------|----------------------------|
| 00 | 01 | 10 | 11 |
| 01 | 00 | 11 | 10 |
| 10 | 11 | 00 | 01 |
| 11 | 10 | 01 | 00 |

LINEAR BURST ADDRESS TABLE (MODE = V_{SS})



ABSOLUTE MAXIMUM RATINGS⁽¹⁾

| Symbol | Parameter | Value | Unit |
|------------------------------------|---|--------------------------------|------|
| T _{STG} | Storage Temperature | -65 to +150 | °C |
| P _D | Power Dissipation | 1.6 | W |
| I _{OUT} | Output Current (per I/O) | 100 | mA |
| V _{IN} , V _{OUT} | Voltage Relative to V _{SS} for I/O Pins | -0.5 to V _{DDQ} + 0.3 | V |
| V _{IN} | Voltage Relative to V _{SS} for for Address and Control Inputs | -0.3 to 4.6 | V |

Notes:

1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
2. This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, precautions may be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit.
3. This device contains circuitry that will ensure the output devices are in High-Z at power up.

OPERATING RANGE (IS61NLFx)

| Range | Ambient Temperature | V _{DD} | V _{DDQ} |
|------------|---------------------|-----------------|------------------|
| Commercial | 0°C to +70°C | 3.3V ± 5% | 3.3V / 2.5V ± 5% |
| Industrial | -40°C to +85°C | 3.3V ± 5% | 3.3V / 2.5V ± 5% |

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OPERATING RANGE (IS61NVFx)

| Range | Ambient Temperature | V _{DD} | V _{DDQ} |
|------------|---------------------|-----------------|------------------|
| Commercial | 0°C to +70°C | 2.5V ± 5% | 2.5V ± 5% |
| Industrial | -40°C to +85°C | 2.5V ± 5% | 2.5V ± 5% |

DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

| Symbol | Parameter | Test Conditions | 3.3V | | 2.5V | | Unit |
|-----------------|------------------------|--|------|-----------------------|------|-----------------------|------|
| | | | Min. | Max. | Min. | Max. | |
| V _{OH} | Output HIGH Voltage | I _{OH} = -4.0 mA (3.3V) I _{OH} = -1.0 mA (2.5V) | 2.4 | — | 2.0 | — | V |
| V _{OL} | Output LOW Voltage | I _{OL} = 8.0 mA (3.3V) I _{OL} = 1.0 mA (2.5V) | — | 0.4 | — | 0.4 | V |
| V _{IH} | Input HIGH Voltage | | 2.0 | V _{DD} + 0.3 | 1.7 | V _{DD} + 0.3 | V |
| V _{IL} | Input LOW Voltage | | -0.3 | 0.8 | -0.3 | 0.7 | V |
| I _{LI} | Input Leakage Current | V _{SS} ≤ V _{IN} ≤ V _{DD} ⁽¹⁾ | -5 | 5 | -5 | 5 | μA |
| I _{LO} | Output Leakage Current | V _{SS} ≤ V _{OUT} ≤ V _{DDQ} , OE = V _{IH} | -5 | 5 | -5 | 5 | μA |

POWER SUPPLY CHARACTERISTICS⁽¹⁾ (Over Operating Range)

| Symbol | Parameter | Test Conditions | Temp. range | 6.5 MAX | | 7.5 MAX | | Unit |
|------------------|--------------------------------|--|---------------------|------------|-----|------------|-----|------|
| | | | | x18 | x36 | x18 | x36 | |
| I _{CC} | AC Operating Supply Current | Device Selected, | Com. | 175 | 175 | 155 | 155 | mA |
| | | OE = V _{IH} , ZZ ≤ V _{IL} , All Inputs ≤ 0.2V or ≥ V _{DD} - 0.2V, Cycle Time ≥ t _{kc} min. | Ind. | 180 | 180 | 160 | 160 | |
| | | | typ. ⁽²⁾ | 120 | | 110 | | |
| I _{SB} | Standby Current TTL Input | Device Deselected, | Com. | 90 | 90 | 90 | 90 | mA |
| | | V _{DD} = Max., All Inputs ≤ V _{IL} or ≥ V _{IH} , ZZ ≤ V _{IL} , f = Max. | Ind. | 100 | 100 | 100 | 100 | |
| I _{SB1} | Standby Current CMOS Input | Device Deselected, | Com. | 70 | 70 | 70 | 70 | mA |
| | | V _{DD} = Max., V _{IN} ≤ V _{SS} + 0.2V or ≥ V _{DD} - 0.2V f = 0 | Ind. | 75 | 75 | 75 | 75 | |
| | | | typ. ⁽²⁾ | 40 | | 40 | | |
| I _{SB2} | Sleep Mode | ZZ > V _{IH} | Com. | 30 | 30 | 30 | 30 | mA |
| | | | Ind. | 35 | 35 | 35 | 35 | |
| | | | typ. ⁽²⁾ | 20 | | 20 | | |

Note:

- MODE pin has an internal pullup and should be tied to V_{DD} or V_{SS}. It exhibits ±100 μA maximum leakage current when tied to ≤ V_{SS} + 0.2V or ≥ V_{DD} - 0.2V.
- Typical values are measured at V_{DD} = 3.3V, T_A = 25°C and not 100% tested.

CAPACITANCE^(1,2)

| Symbol | Parameter | Conditions | Max. | Unit |
|------------------|--------------------------|-----------------------|------|------|
| C _{IN} | Input Capacitance | V _{IN} = 0V | 6 | pF |
| C _{OUT} | Input/Output Capacitance | V _{OUT} = 0V | 8 | pF |

Notes:

1. Tested initially and after any design or process changes that may affect these parameters.
2. Test conditions: T_A = 25°C, f = 1 MHz, V_{DD} = 3.3V.

3.3V I/O AC TEST CONDITIONS

| Parameter | Unit |
|---|---------------------|
| Input Pulse Level | 0V to 3.0V |
| Input Rise and Fall Times | 1.5 ns |
| Input and Output Timing and Reference Level | 1.5V |
| Output Load | See Figures 1 and 2 |

3.3V I/O OUTPUT LOAD EQUIVALENT



Figure 1



Figure 2

2.5V I/O AC TEST CONDITIONS

| Parameter | Unit |
|---|---------------------|
| Input Pulse Level | 0V to 2.5V |
| Input Rise and Fall Times | 1.5 ns |
| Input and Output Timing and Reference Level | 1.25V |
| Output Load | See Figures 3 and 4 |

2.5V I/O OUTPUT LOAD EQUIVALENT



Figure 3



Figure 4

READ/WRITE CYCLE SWITCHING CHARACTERISTICS⁽¹⁾ (Over Operating Range)

| Symbol | Parameter | 6.5 | | 7.5 | | Unit |
|------------------------|---------------------------------|------|------|------|------|------|
| | | Min. | Max. | Min. | Max. | |
| fmax | Clock Frequency | — | 133 | — | 117 | MHz |
| tkc | Cycle Time | 7.5 | — | 8.5 | — | ns |
| tkH | Clock High Time | 2.2 | — | 2.5 | — | ns |
| tkL | Clock Low Time | 2.2 | — | 2.5 | — | ns |
| tkQ | Clock Access Time | — | 6.5 | — | 7.5 | ns |
| tkQX ⁽²⁾ | Clock High to Output Invalid | 2.5 | — | 2.5 | — | ns |
| tkQLZ ^(2,3) | Clock High to Output Low-Z | 2.5 | — | 2.5 | — | ns |
| tkQHZ ^(2,3) | Clock High to Output High-Z | — | 3.8 | — | 4.0 | ns |
| toEQ | Output Enable to Output Valid | — | 3.2 | — | 3.4 | ns |
| toELZ ^(2,3) | Output Enable to Output Low-Z | 0 | — | 0 | — | ns |
| toEHZ ^(2,3) | Output Disable to Output High-Z | — | 3.5 | — | 3.5 | ns |
| tAS | Address Setup Time | 1.5 | — | 1.5 | — | ns |
| tWS | Read/Write Setup Time | 1.5 | — | 1.5 | — | ns |
| tCES | Chip Enable Setup Time | 1.5 | — | 1.5 | — | ns |
| tSE | Clock Enable Setup Time | 1.5 | — | 1.5 | — | ns |
| tADVS | Address Advance Setup Time | 1.5 | — | 1.5 | — | ns |
| tDS | Data Setup Time | 1.5 | — | 1.5 | — | ns |
| tAH | Address Hold Time | 0.5 | — | 0.5 | — | ns |
| tHE | Clock Enable Hold Time | 0.5 | — | 0.5 | — | ns |
| tWH | Write Hold Time | 0.5 | — | 0.5 | — | ns |
| tCEH | Chip Enable Hold Time | 0.5 | — | 0.5 | — | ns |
| tADVH | Address Advance Hold Time | 0.5 | — | 0.5 | — | ns |
| tDH | Data Hold Time | 0.5 | — | 0.5 | — | ns |
| tpDS | ZZ High to Power Down | — | 2 | — | 2 | cyc |
| tpUS | ZZ Low to Power Down | — | 2 | — | 2 | cyc |

Notes:

1. Configuration signal MODE is static and must not change during normal operation.
2. Guaranteed but not 100% tested. This parameter is periodically sampled.
3. Tested with load in Figure 2.

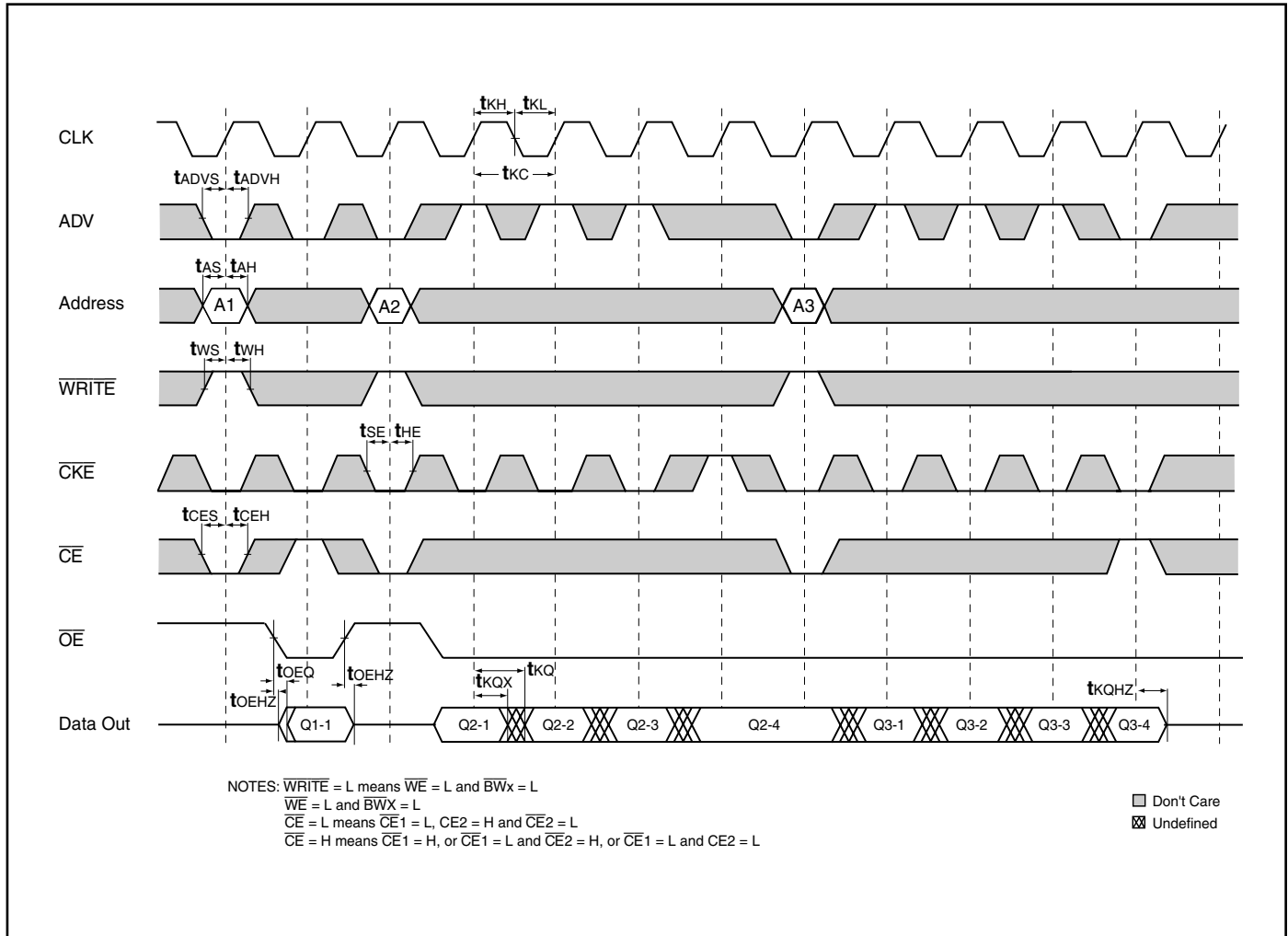
SLEEP MODE ELECTRICAL CHARACTERISTICS

| Symbol | Parameter | Conditions | Min. | Max. | Unit |
|------------------|-----------------------------------|----------------------|------|------|-------|
| I _{SB2} | Current during SLEEP MODE | ZZ ≥ V _{IH} | | 35 | mA |
| t _{PDS} | ZZ active to input ignored | | | 2 | cycle |
| t _{PUS} | ZZ inactive to input sampled | | 2 | | cycle |
| t _{ZZI} | ZZ active to SLEEP current | | 2 | | cycle |
| t _{ZZI} | ZZ inactive to exit SLEEP current | | 0 | | ns |

SLEEP MODE TIMING



READ CYCLE TIMING



WRITE CYCLE TIMING



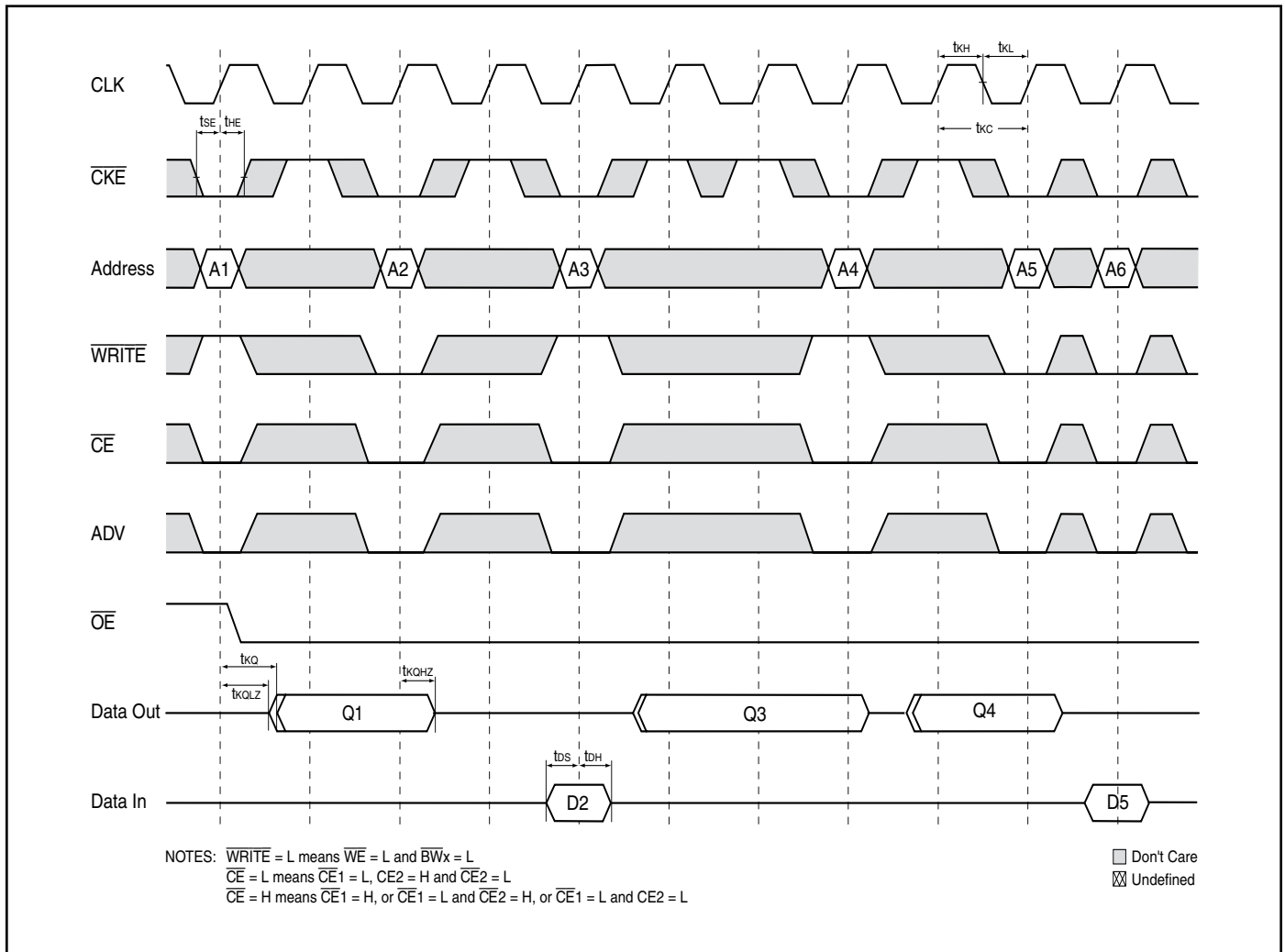
SINGLE READ/WRITE CYCLE TIMING



NOTES: $\overline{WRITE} = L$ means $\overline{WE} = L$ and $\overline{BWx} = L$
 $\overline{CE} = L$ means $\overline{CE1} = L$, $CE2 = H$ and $\overline{CE2} = L$
 $\overline{CE} = H$ means $\overline{CE1} = H$, or $\overline{CE1} = L$ and $CE2 = H$, or $\overline{CE1} = L$ and $\overline{CE2} = L$

□ Don't Care
 ▨ Undefined

CKE OPERATION TIMING



CE OPERATION TIMING





IS61NLF12836A/IS61NVF12836A
IS61NLF25618A/IS61NVF25618A

ORDERING INFORMATION ($V_{DD} = 3.3V/V_{DDQ} = 2.5V/3.3V$)
Commercial Range: 0°C to +70°C

| Access Time | Order Part Number | Package |
|----------------|---------------------|----------|
| 128Kx36 | | |
| 6.5 | IS61NLF12836A-6.5TQ | 100 TQFP |
| | IS61NLF12836A-6.5B2 | 119 PBGA |
| | IS61NLF12836A-6.5B3 | 165 PBGA |
| 7.5 | IS61NLF12836A-7.5TQ | 100 TQFP |
| | IS61NLF12836A-7.5B2 | 119 PBGA |
| | IS61NLF12836A-7.5B3 | 165 PBGA |
| 256Kx18 | | |
| 6.5 | IS61NLF25618A-6.5TQ | 100 TQFP |
| | IS61NLF25618A-6.5B2 | 119 PBGA |
| | IS61NLF25618A-6.5B3 | 165 PBGA |
| 7.5 | IS61NLF25618A-7.5TQ | 100 TQFP |
| | IS61NLF25618A-7.5B2 | 119 PBGA |
| | IS61NLF25618A-7.5B3 | 165 PBGA |

Industrial Range: -40°C to +85°C

| Access Time | Order Part Number | Package |
|----------------|-----------------------|---------------------|
| 128Kx36 | | |
| 6.5 | IS61NLF12836A-6.5TQI | 100 TQFP |
| | IS61NLF12836A-6.5B2I | 119 PBGA |
| | IS61NLF12836A-6.5B3I | 165 PBGA |
| 7.5 | IS61NLF12836A-7.5TQI | 100 TQFP |
| | IS61NLF12836A-7.5TQLI | 100 TQFP, Lead-free |
| | IS61NLF12836A-7.5B2I | 119 PBGA |
| | IS61NLF12836A-7.5B3I | 165 PBGA |
| | IS61NLF12836A-7.5B3LI | 165 PBGA, Lead-free |
| 256Kx18 | | |
| 6.5 | IS61NLF25618A-6.5TQI | 100 TQFP |
| | IS61NLF25618A-6.5B2I | 119 PBGA |
| | IS61NLF25618A-6.5B3I | 165 PBGA |
| 7.5 | IS61NLF25618A-7.5TQI | 100 TQFP |
| | IS61NLF25618A-7.5TQLI | 100 TQFP, Lead-free |
| | IS61NLF25618A-7.5B2I | 119 PBGA |
| | IS61NLF25618A-7.5B3I | 165 PBGA |

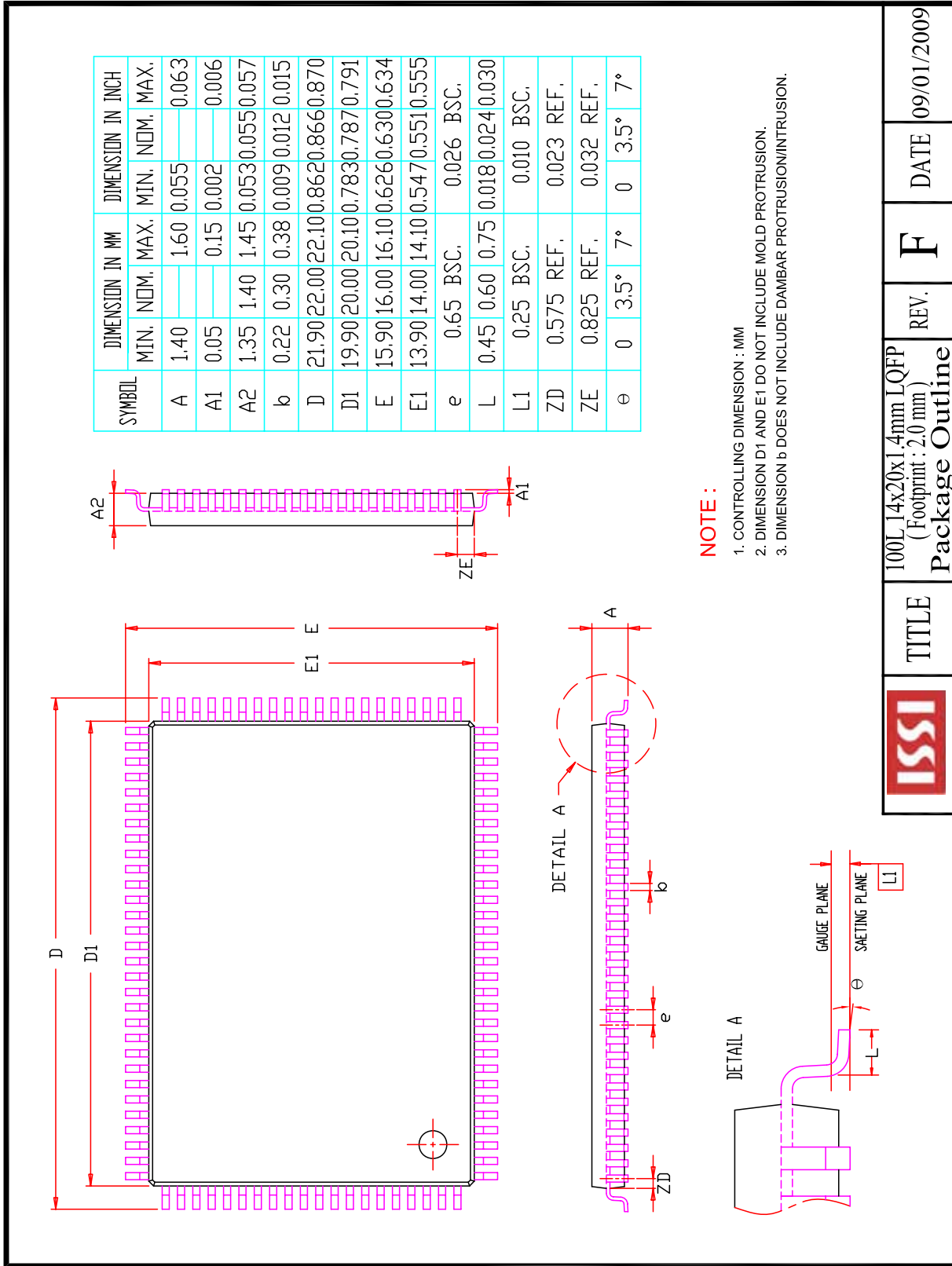
ORDERING INFORMATION (V_{DD} = 2.5V/V_{DDQ} = 2.5V)

Commercial Range: 0°C to +70°C

| Access Time | Order Part Number | Package |
|----------------|---------------------|----------|
| 128Kx36 | | |
| 6.5 | IS61NVF12836A-6.5TQ | 100 TQFP |
| | IS61NVF12836A-6.5B2 | 119 PBGA |
| | IS61NVF12836A-6.5B3 | 165 PBGA |
| 7.5 | IS61NVF12836A-7.5TQ | 100 TQFP |
| | IS61NVF12836A-7.5B2 | 119 PBGA |
| | IS61NVF12836A-7.5B3 | 165 PBGA |
| 256Kx18 | | |
| 6.5 | IS61NVF25618A-6.5TQ | 100 TQFP |
| | IS61NVF25618A-6.5B2 | 119 PBGA |
| | IS61NVF25618A-6.5B3 | 165 PBGA |
| 7.5 | IS61NVF25618A-7.5TQ | 100 TQFP |
| | IS61NVF25618A-7.5B2 | 119 PBGA |
| | IS61NVF25618A-7.5B3 | 165 PBGA |

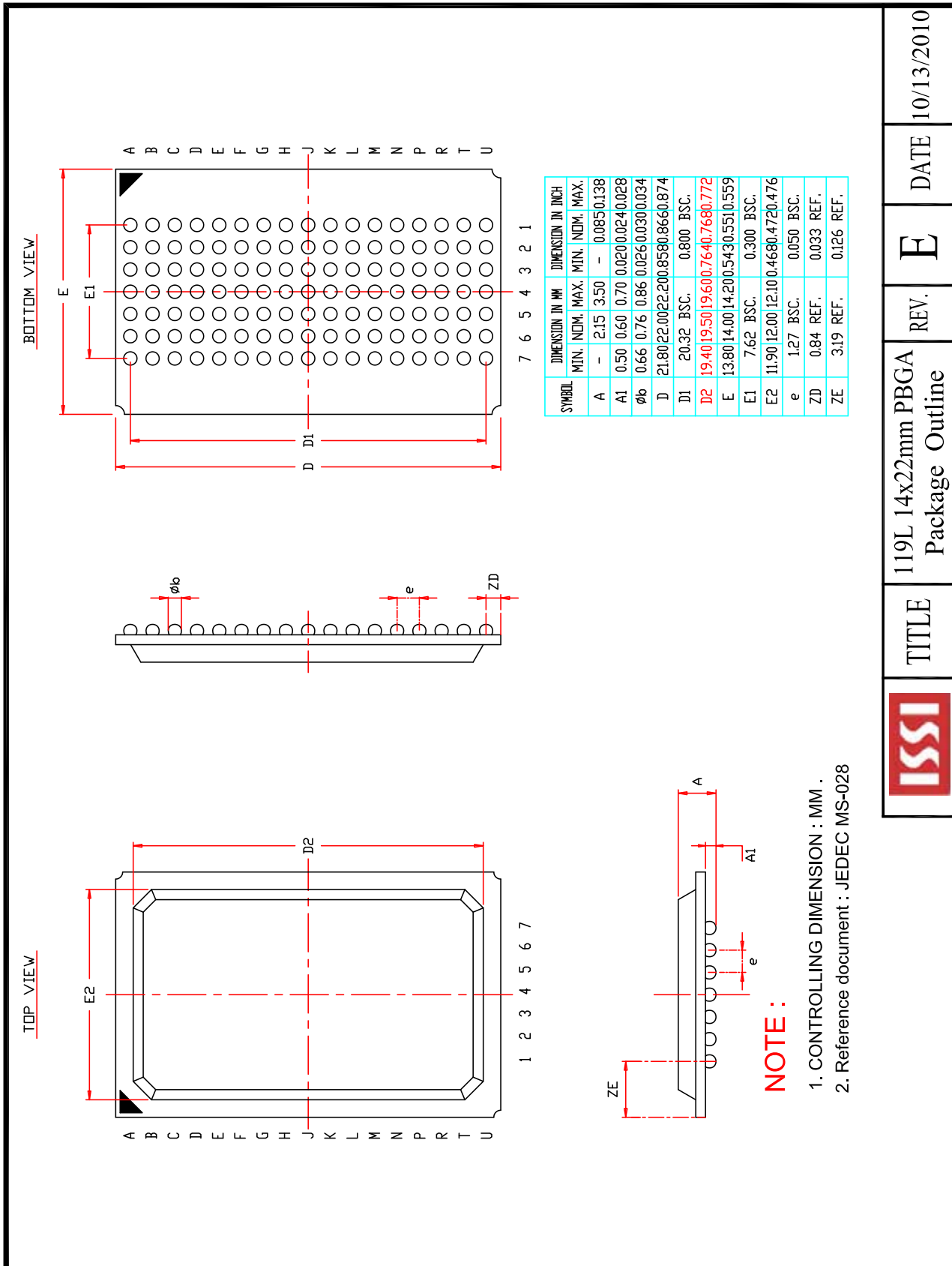
Industrial Range: -40°C to +85°C

| Access Time | Order Part Number | Package |
|----------------|----------------------|----------|
| 128Kx36 | | |
| 6.5 | IS61NVF12836A-6.5TQI | 100 TQFP |
| | IS61NVF12836A-6.5B2I | 119 PBGA |
| | IS61NVF12836A-6.5B3I | 165 PBGA |
| 7.5 | IS61NVF12836A-7.5TQI | 100 TQFP |
| | IS61NVF12836A-7.5B2I | 119 PBGA |
| | IS61NVF12836A-7.5B3I | 165 PBGA |
| 256Kx18 | | |
| 6.5 | IS61NVF25618A-6.5TQI | 100 TQFP |
| | IS61NVF25618A-6.5B2I | 119 PBGA |
| | IS61NVF25618A-6.5B3I | 165 PBGA |
| 7.5 | IS61NVF25618A-7.5TQI | 100 TQFP |
| | IS61NVF25618A-7.5B2I | 119 PBGA |
| | IS61NVF25618A-7.5B3I | 165 PBGA |

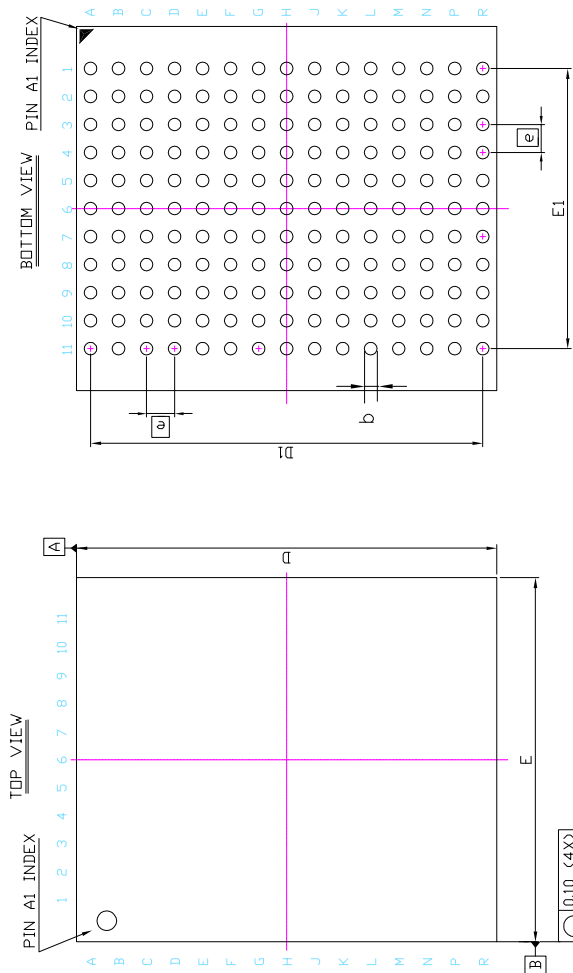


| | | | | |
|--|-------|--|--------|-----------------|
| | TITLE | 100L 14x20x1.4mm LQFP (Footprint : 2.0 mm) Package Outline | REV. F | DATE 09/01/2009 |
|--|-------|--|--------|-----------------|

280-600-011 REV. A



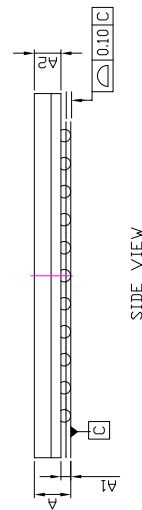
| | | | |
|--|--------------------------------------|------|------------|
| | TITLE | REV. | DATE |
| | 119L 14x22mm PBGA Package Outline | E | 10/13/2010 |



| SYM. | DIMENSION (mm) | | | DIMENSION (inch) | | |
|-----------|----------------|-------|-------|------------------|-------|-------|
| | MIN. | NOM. | MAX. | MIN. | NOM. | MAX. |
| A | — | — | 1.20 | — | — | 0.047 |
| A1 | 0.25 | 0.35 | 0.40 | 0.010 | 0.014 | 0.016 |
| A2 | — | 0.79 | — | — | 0.031 | — |
| b | 0.40 | 0.45 | 0.50 | 0.016 | 0.018 | 0.020 |
| D | 14.90 | 15.00 | 15.10 | 0.587 | 0.591 | 0.594 |
| DI | 13.90 | 14.00 | 14.10 | 0.547 | 0.551 | 0.555 |
| E | 12.90 | 13.00 | 13.10 | 0.508 | 0.512 | 0.516 |
| E1 | 9.90 | 10.00 | 10.10 | 0.390 | 0.394 | 0.398 |
| \square | 1.00 BSC | | | 0.039 BSC | | |

NOTE :

1. CONTROLLING DIMENSION : MM .



| | | | | |
|--|-------|--|--------|-----------------|
| | TITLE | 165L 13x15mm TF-BGA Package Outline | REV. B | DATE 08/28/2008 |
|--|-------|--|--------|-----------------|

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